



DOCKET NO.: 0057-2533-2YY CONT

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

PRERE APPLICATION OF

HIDEKI TAKAHASHI

: EXAMINER: LOKE, S.

SERIAL NO: 09/421,217

RCE FILED: MARCH 6, 2003

: GROUP ART UNIT: 2811

FOR: INSULATED GATE
SEMICONDUCTOR DEVICE
WITH LOW ON VOLTAGE AND
MANUFACTURING METHOD
THEREOF

AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA. 22313

SIR:

In response to the Office Action of April 21, 2003, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel Claims 22-26 without prejudice.¹

Please amend Claim 40 to read as follows:

figs. 3, 22, 23
40. (Amended) An insulated gate semiconductor device, comprising:
a first semiconductor layer of a first conductivity type having first and second main surfaces on opposite sides thereof;
a second semiconductor layer of a second conductivity type provided on said first main surface of said first semiconductor layer;

¹ A marked-up copy of the amendments is attached hereto.

#27/G

7/29/03

Adm H

RECEIVED
JUL 22 2003
TECHNOLOGY CENTER 2800